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# FSEZ1317A

## Primary-Side-Regulation PWM with POWER MOSFET Integrated

### Features

- Low Standby Power Under 30mW
- High-Voltage Startup
- Fewest External Component Counts
- Constant-Voltage (CV) and Constant-Current (CC) Control without Secondary-Feedback Circuitry
- Green-Mode: Linearly Decreasing PWM Frequency
- Fixed PWM Frequency at 50kHz with Frequency Hopping to Solve EMI Problem
- Cable Compensation in CV Mode
- Peak-Current-Mode Control in CV Mode
- Cycle-by-Cycle Current Limiting
- $V_{DD}$  Over-Voltage Protection with Auto Restart
- $V_{DD}$  Under-Voltage Lockout (UVLO)
- Gate Output Maximum Voltage Clamped at 15V
- Fixed Over-Temperature Protection with Auto Restart
- Available in the 7-Lead SOP Package

### Applications

- Battery chargers for cellular phones, cordless phones, PDA, digital cameras, power tools, etc.
- Replaces linear transformers and RCC SMPS

### Related Resources

- [Evaluation Board: FEBFSEZ1317A\\_CH310v3](#)
- [Fairchild Power Supply WebDesigner — Flyback Design & Simulation - In Minutes at No Expense](#)

### Description

This third-generation Primary-Side-Regulation (PSR) and highly integrated PWM controller provides several features to enhance the performance of low-power flyback converters. The proprietary topology, TRUECURRENT<sup>®</sup>, of FSEZ1317A enables precise CC regulation and simplified circuit design for battery-charger applications. A low-cost, smaller, and lighter charger results, as compared to a conventional design or a linear transformer.

To minimize standby power consumption, the proprietary green mode provides off-time modulation to linearly decrease PWM frequency under light-load conditions. Green mode assists the power supply in meeting power conservation requirements.

By using the FSEZ1317A, a charger can be implemented with few external components and minimized cost. A typical output CV/CC characteristic envelope is shown in Figure 1.

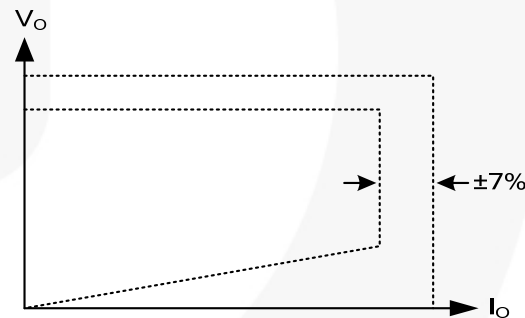


Figure 1. Typical Output V-I Characteristic

### Ordering Information

Part Number	Operating Temperature Range	Package	Packing Method
FSEZ1317AMY_F116	-40°C to +105°C	7-Lead, Small Outline Package (SOP-7)	Tape & Reel

### Application Diagram

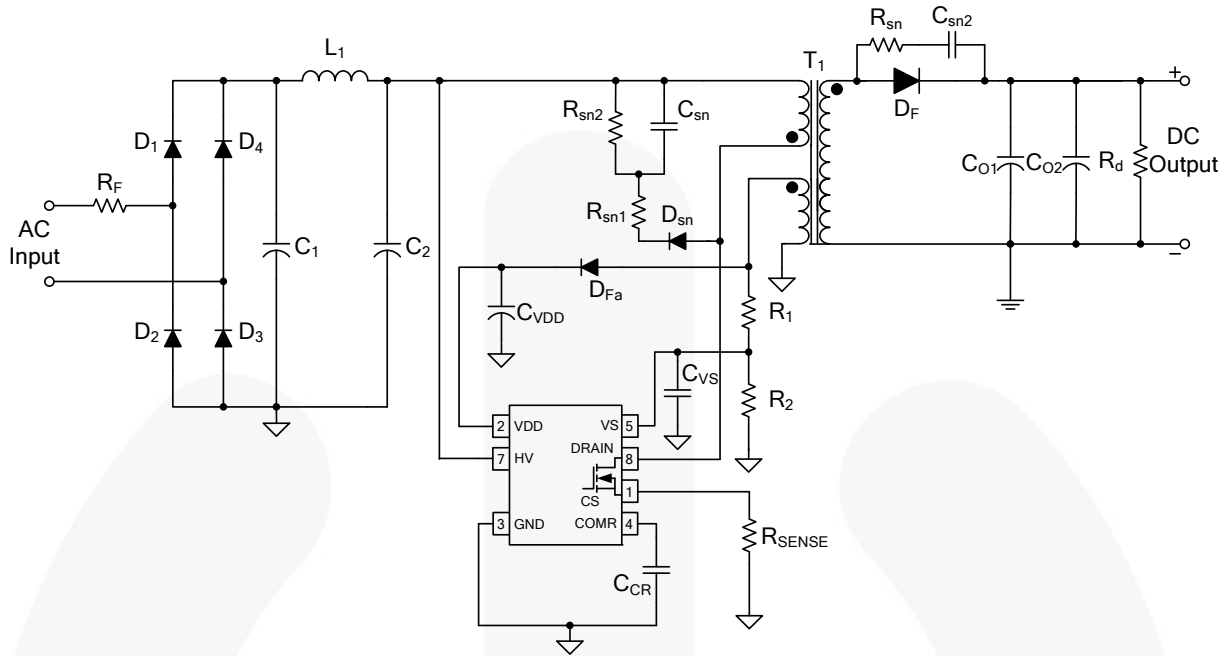


Figure 2. Typical Application

### Internal Block Diagram

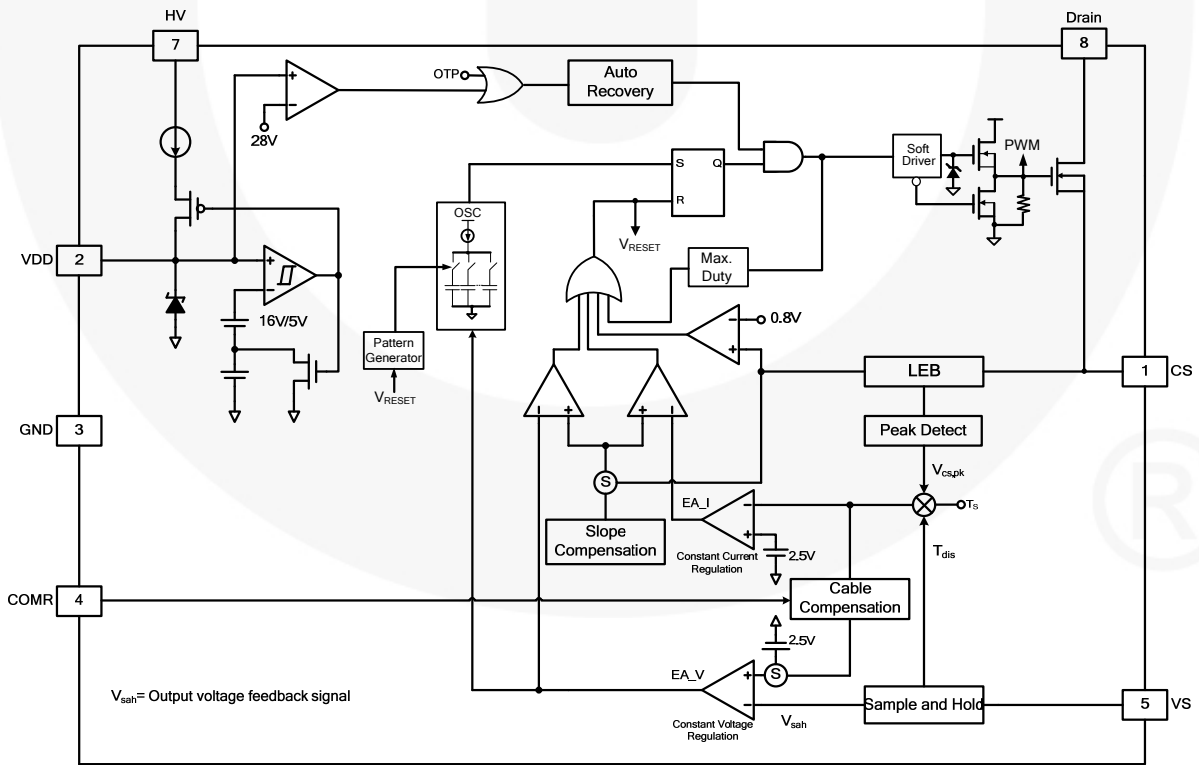
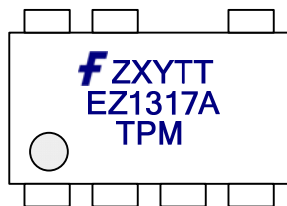


Figure 3. Functional Block Diagram

## Marking Information



F: Fairchild Logo  
 Z: Plant Code  
 X: 1-Digit Year Code  
 Y: 1-Digit Week Code  
 TT: 2-Digit Die Run Code  
 T: Package Type (M=SOP)  
 P: Y=Green Package  
 M: Manufacture Flow Code

Figure 4. Top Mark

## Pin Configuration

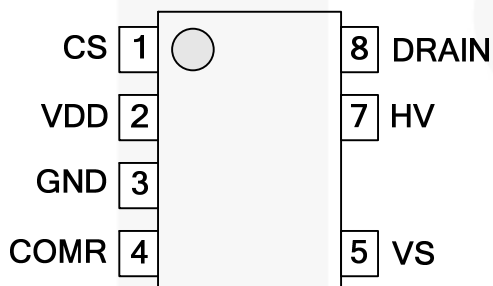


Figure 5. Pin Configuration

## Pin Definitions

Pin #	Name	Description
1	CS	<b>Current Sense.</b> This pin connects a current-sense resistor, to detect the MOSFET current for peak-current-mode control in CV mode, and provides the output-current regulation in CC mode.
2	VDD	<b>Power Supply.</b> IC operating current and MOSFET driving current are supplied using this pin. This pin is connected to an external $V_{DD}$ capacitor of typically $10\mu\text{F}$ . The threshold voltages for startup and turn-off are 16V and 5V, respectively. The operating current is lower than 5mA.
3	GND	<b>Ground</b>
4	COMR	<b>Cable Compensation.</b> This pin connects a $1\mu\text{F}$ capacitor between the COMR and GND pins for compensation voltage drop due to output cable loss in CV mode.
5	VS	<b>Voltage Sense.</b> This pin detects the output voltage information and discharge time based on voltage of auxiliary winding.
7	HV	<b>High Voltage.</b> This pin connects to bulk capacitor for high-voltage startup.
8	DRAIN	<b>Driver Output.</b> Power MOSFET drain. This pin is the high-voltage power MOSFET drain.

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter		Min.	Max.	Units
V <sub>HV</sub>	HV Pin Input Voltage			500	V
V <sub>VDD</sub>	DC Supply Voltage <sup>(1,2)</sup>			30	V
V <sub>VS</sub>	VS Pin Input Voltage		-0.3	7.0	V
V <sub>CS</sub>	CS Pin Input Voltage		-0.3	7.0	V
V <sub>COMV</sub>	Voltage Error Amplifier Output Voltage		-0.3	7.0	V
V <sub>COMI</sub>	Current Error Amplifier Output Voltage		-0.3	7.0	V
V <sub>DS</sub>	Drain-Source Voltage			700	V
I <sub>D</sub>	Continuous Drain Current	T <sub>A</sub> =25°C		1	A
		T <sub>A</sub> =100°C		0.6	A
I <sub>DM</sub>	Pulsed Drain Current			4	A
E <sub>AS</sub>	Single Pulse Avalanche Energy			50	mJ
I <sub>AR</sub>	Avalanche Current			1	A
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> <50°C)			660	mW
θ <sub>JA</sub>	Thermal Resistance (Junction-to-Air)			150	°C/W
Ψ <sub>JT</sub>	Thermal Resistance (Junction-to-Case)			39	°C/W
T <sub>J</sub>	Operating Junction Temperature		-40	+150	°C
T <sub>STG</sub>	Storage Temperature Range		-55	+150	°C
T <sub>L</sub>	Lead Temperature (Wave soldering or IR, 10 seconds)			+260	°C
ESD	Electrostatic Discharge Capability (Except HV Pin)	Human Body Model, JEDEC-JESD22_A114	5000		V
		Charged Device Model, JEDEC-JESD22_C101	2000		

### Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.
2. All voltage values, except differential voltages, are given with respect to the GND pin.
3. ESD ratings including HV pin: HBM=500V, CDM=1250V.

## Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Units
T <sub>A</sub>	Operating Ambient Temperature	-40	+105	°C

## Electrical Characteristics

Unless otherwise specified,  $V_{DD}=15V$  and  $T_A=25^{\circ}C$ .

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units	
<b>V<sub>DD</sub> Section</b>							
V <sub>OP</sub>	Continuously Operating Voltage				23	V	
V <sub>DD-ON</sub>	Turn-On Threshold Voltage		15	16	17	V	
V <sub>DD-OFF</sub>	Turn-Off Threshold Voltage		4.5	5.0	5.5	V	
I <sub>DD-OP</sub>	Operating Current			2.5	5.0	mA	
I <sub>DD-GREEN</sub>	Green-Mode Operating Supply Current			0.95	1.45	mA	
V <sub>DD-OVP</sub>	V <sub>DD</sub> Over-Voltage-Protection Level (OVP)			24		V	
V <sub>DD-OVP-HYS</sub>	Hysteresis Voltage for V <sub>DD</sub> OVP		1.5	2.0	2.5	V	
t <sub>D-VDDOVP</sub>	V <sub>DD</sub> Over-Voltage-Protection Debounce Time		50	200	300	μs	
<b>HV Startup Current Source Section</b>							
V <sub>HV-MIN</sub>	Minimum Startup Voltage on HV Pin				50	V	
I <sub>HV</sub>	Supply Current Drawn from HV Pin	V <sub>DC</sub> =100V		1.5	3.0	mA	
I <sub>HV-LC</sub>	Leakage Current after Startup	HV=500V, V <sub>DD</sub> = V <sub>DD-OFF</sub> +1V		0.96	3.00	μA	
<b>Oscillator Section</b>							
f <sub>OSC</sub>	Frequency	Center Frequency		47	50	53	kHz
		Frequency Hopping Range			±3.5		
f <sub>OSC-N-MIN</sub>	Minimum Frequency at No-Load				370	Hz	
f <sub>OSC-CM-MIN</sub>	Minimum Frequency at CCM				13	kHz	
f <sub>DV</sub>	Frequency Variation vs. V <sub>DD</sub> Deviation	V <sub>DD</sub> =10~25V,			1	2	%
f <sub>DT</sub>	Frequency Variation vs. Temperature Deviation	T <sub>A</sub> =-40°C to 105°C				15	%
<b>Voltage-Sense Section</b>							
I <sub>IC</sub>	IC Bias Current				10	μA	
V <sub>BIAS-COMV</sub>	Adaptive Bias Voltage Dominated by V <sub>COMV</sub>	R <sub>VS</sub> =20kΩ			1.4	V	
<b>Current-Sense Section</b>							
t <sub>PD</sub>	Propagation Delay to GATE Output				90	200	ns
t <sub>MIN-N</sub>	Minimum On Time at No-Load		590	795	1000		ns
V <sub>TH</sub>	Threshold Voltage for Current Limit				0.8		V
<b>Voltage-Error-Amplifier Section</b>							
V <sub>VR</sub>	Reference Voltage		2.475	2.500	2.525		V
V <sub>N</sub>	Green-Mode Starting Voltage on EA_V	f <sub>OSC</sub> =5kHz			2.2		V
V <sub>G</sub>	Green-Mode Ending Voltage on EA_V	f <sub>OSC</sub> =1kHz			0.4		V
<b>Current-Error-Amplifier Section</b>							
V <sub>IR</sub>	Reference Voltage		2.475	2.500	2.525		V
<b>Cable Compensation Section</b>							
V <sub>COMR</sub>	COMR Pin for Cable Compensation				0.85		V

Continued on the following page...

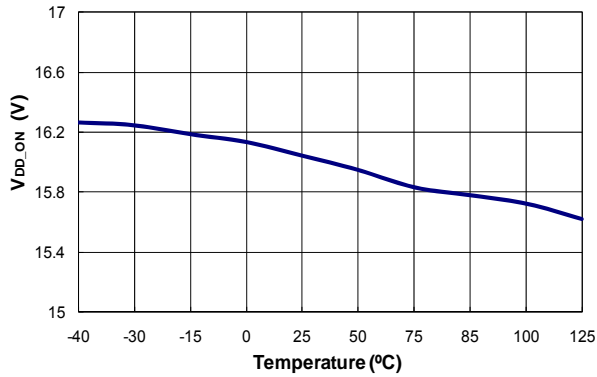
**Electrical Characteristics** (Continued)Unless otherwise specified,  $V_{DD}=15V$  and  $T_A=25^\circ C$ .

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
<b>Internal MOSFET Section<sup>(4)</sup></b>						
$DCY_{MAX}$	Maximum Duty Cycle		52	65	78	%
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu A$ , $V_{GS}=0V$	700			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D=250\mu A$ , Referenced to $T_A=25^\circ C$		0.53		V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$I_D=0.5A$ , $V_{GS}=10V$		13	16	$\Omega$
$I_S$	Maximum Continuous Drain-Source Diode Forward Current				1	A
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=700V$ , $T_A=25^\circ C$			10	$\mu A$
		$V_{DS}=560V$ , $T_A=100^\circ C$			100	$\mu A$
$t_{D-ON}$	Turn-On Delay Time	$V_{DS}=350V$ , $I_D=1A$ ,		10	30	ns
$t_{D-OFF}$	Turn-Off Delay Time	$R_G=25\Omega^{(5)}$		20	50	ns
$C_{ISS}$	Input Capacitance	$V_{GS}=0V$ , $V_{DS}=25V$ , $f_S=1MHz$		175	200	pF
$C_{OSS}$	Output Capacitance			23	25	pF
<b>Over-Temperature-Protection Section</b>						
$T_{OTP}$	Threshold Temperature for OTP <sup>(6)</sup>			+140		°C

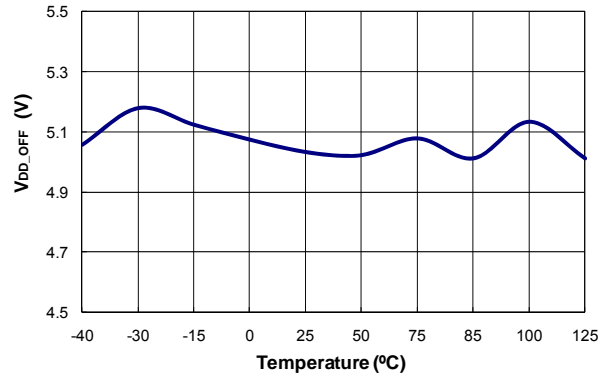
**Notes:**

- These parameters, although guaranteed, are not 100% tested in production.
- Pulse test: pulsewidth  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- When the Over-temperature protection is activated, the power system enter auto-restart mode and output is disabled.

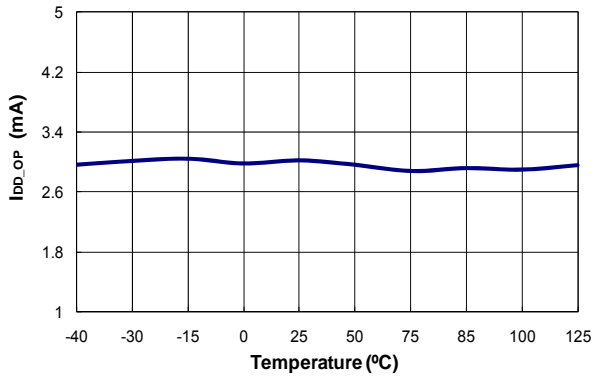
## Typical Performance Characteristics



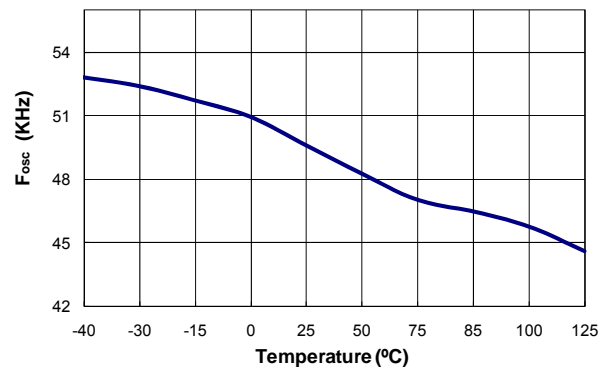
**Figure 6. Turn-On Threshold Voltage ( $V_{DD-ON}$ ) vs. Temperature**



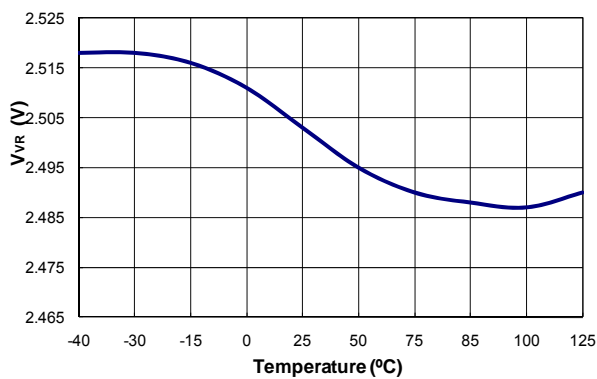
**Figure 7. Turn-Off Threshold Voltage ( $V_{DD-OFF}$ ) vs. Temperature**



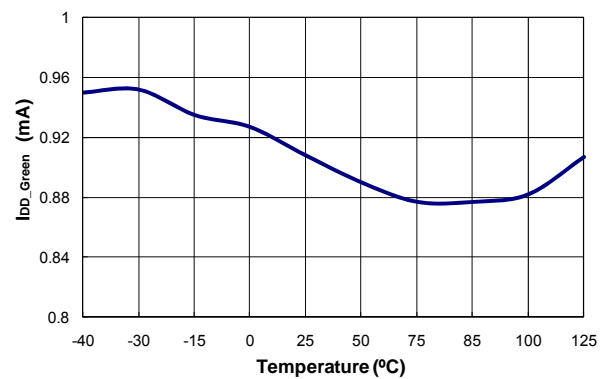
**Figure 8. Operating Current ( $I_{DD-OP}$ ) vs. Temperature**



**Figure 9. Center Frequency ( $f_{OSC}$ ) vs. Temperature**



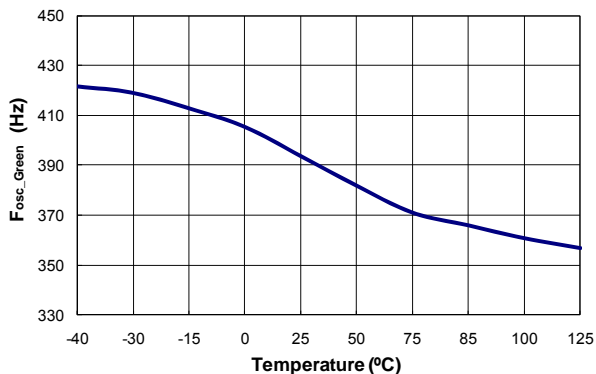
**Figure 10. Reference Voltage ( $V_{VR}$ ) vs. Temperature**



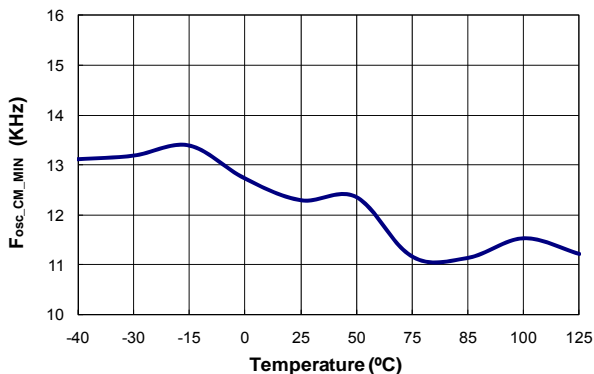
**Figure 11. Green Mode Operating Supply Current ( $I_{DD-GREEN}$ ) vs. Temperature**



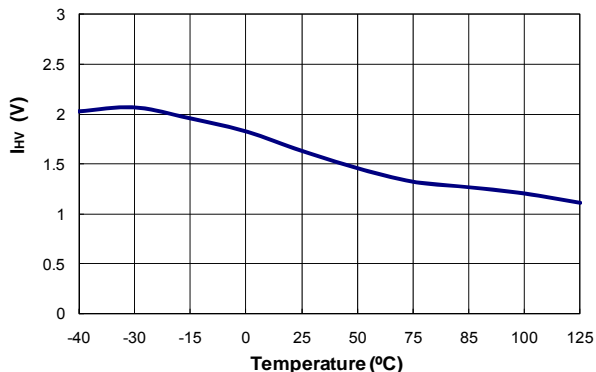
## Typical Performance Characteristics (Continued)



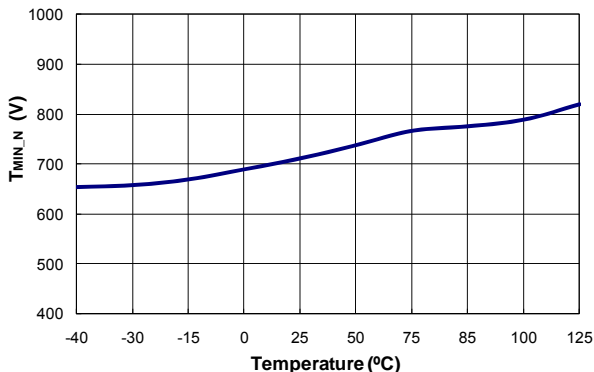
**Figure 12. Minimum Frequency at No Load (f<sub>OSC-N-MIN</sub>) vs. Temperature**



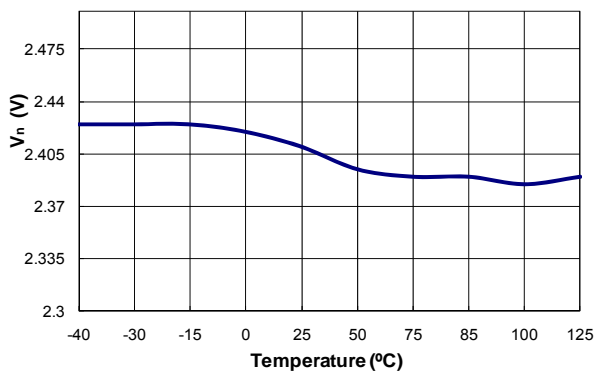
**Figure 13. Minimum Frequency at CCM (f<sub>OSC-CM-MIN</sub>) vs. Temperature**



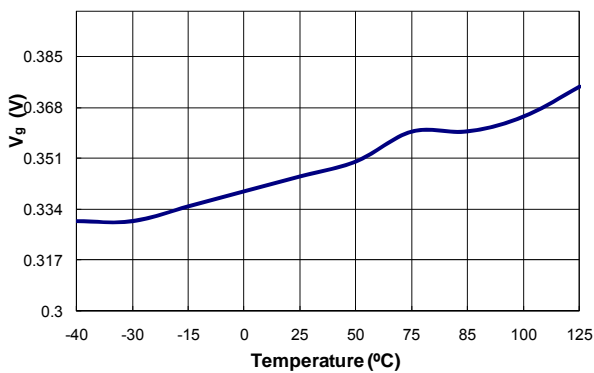
**Figure 14. Supply Current Drawn from HV Pin (I<sub>HV</sub>) vs. Temperature**



**Figure 15. Minimum On Time at No Load (t<sub>MIN-N</sub>) vs. Temperature**



**Figure 16. Green Mode Starting Voltage on EA\_V (V<sub>N</sub>) vs. Temperature**



**Figure 17. Green Mode Ending Voltage on EA\_V (V<sub>G</sub>) vs. Temperature**

### Typical Performance Characteristics (Continued)

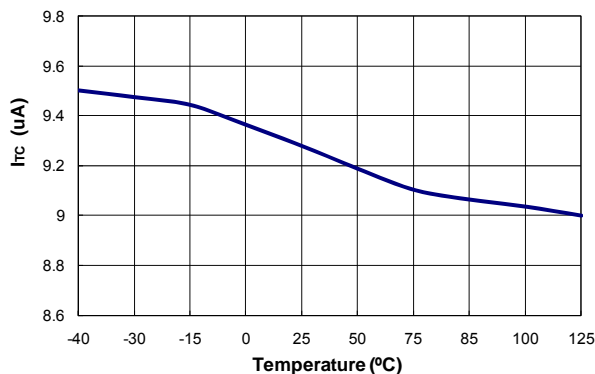


Figure 18. IC Bias Current ( $I_{bc}$ ) vs. Temperature

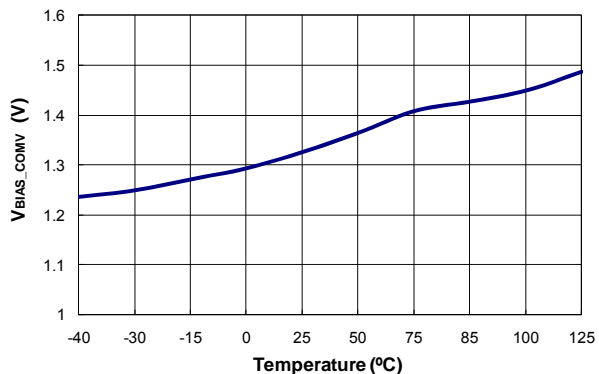


Figure 19. Adaptive Bias Voltage Dominated by  $V_{COMV}$  ( $V_{BIAS-COMV}$ ) vs. Temperature

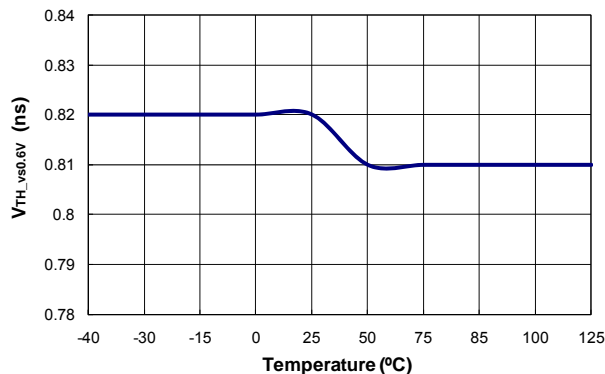


Figure 20. Threshold Voltage for Current Limit ( $V_{TH}$ ) vs. Temperature

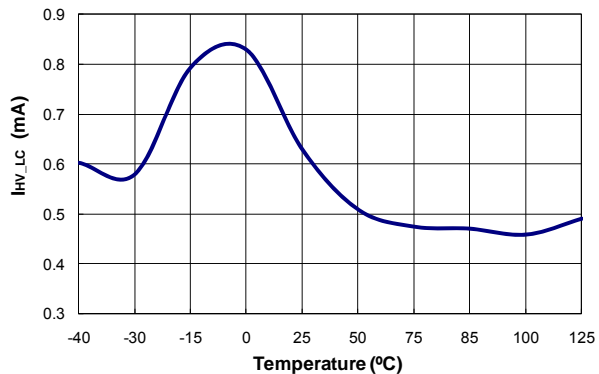


Figure 21. Leakage Current after Startup ( $I_{HV-LC}$ ) vs. Temperature

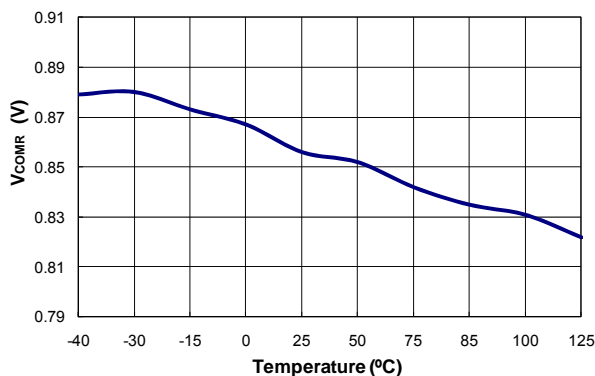


Figure 22. Variation Test Voltage on COMR Pin for Cable Compensation ( $V_{COMR}$ ) vs. Temperature

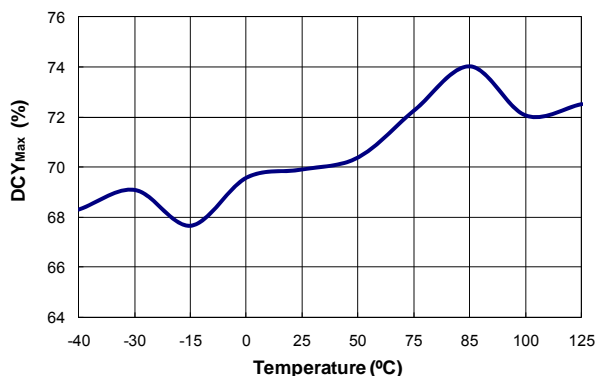


Figure 23. Maximum Duty Cycle ( $DCY_{MAX}$ ) vs. Temperature



### Cable Voltage Drop Compensation

In cellular phone charger applications, the battery is located at the end of cable, which typically causes several percentage of voltage drop on the battery voltage. FSEZ1317A has a built-in cable voltage drop compensation that provides a constant output voltage at the end of the cable over the entire load range in CV mode. As load increases, the voltage drop across the cable is compensated by increasing the reference voltage of the voltage regulation error amplifier.

### Operating Current

Operating current as small as 2.5mA results in higher efficiency and reduces the VDD hold-up capacitance requirement. Once enters “deep” Green Mode, the operating current is reduced to 0.95mA, which helps the power supply meet power conservation requirements

### Green-Mode Operation

The FSEZ1317A uses voltage regulation error amplifier output ( $V_{COMV}$ ) as an indicator of the output load and modulates the PWM frequency as shown in Figure 26. The switching frequency decreases as the load decreases. In heavy load conditions, the switching frequency is fixed at 50kHz. Once  $V_{COMV}$  decreases below 2.5V, the PWM frequency linearly decreases from 50kHz. When FSEZ1317A enters deep green mode, the PWM frequency is reduced to a minimum frequency of 370Hz, thus gaining power saving to meet international power conservation requirements.

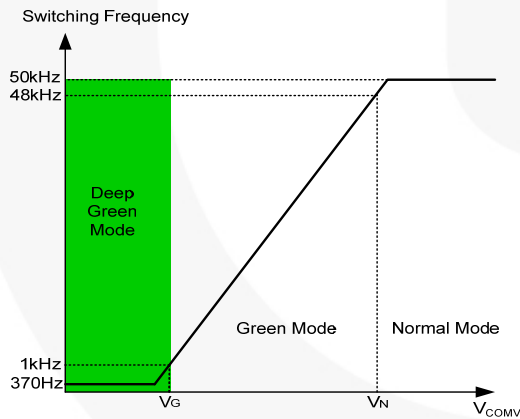


Figure 26. Switching Frequency in Green Mode

### Frequency Hopping

EMI reduction is accomplished by frequency hopping, which spreads the energy over a wider frequency range than the bandwidth measured by the EMI test equipment. FSEZ1317A has an internal frequency hopping circuit that changes the switching frequency between 46kHz and 54kHz over the period shown in Figure 27.

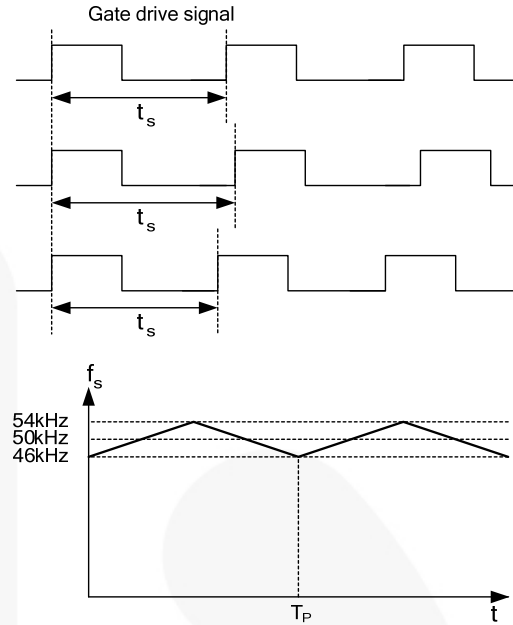


Figure 27. Frequency Hopping

### High-Voltage Startup

Figure 28 shows the HV-startup circuit for FSEZ1317A applications. The HV pin is connected to the line input or bulk capacitor through a resistor,  $R_{START}$  (100kΩ recommended). During startup status, the internal startup circuit is enabled. Meanwhile, line input supplies the current,  $I_{STARTUP}$ , to charge the hold-up capacitor,  $C_{DD}$ , through  $R_{START}$ . When the  $V_{DD}$  voltage reaches  $V_{DD-ON}$ , the internal startup circuit is disabled, blocking  $I_{STARTUP}$  from flowing into the HV pin. Once the IC turns on,  $C_{DD}$  is the only energy source to supply the IC consumption current before the PWM starts to switch. Thus,  $C_{DD}$  must be large enough to prevent  $V_{DD}$  from dropping down to  $V_{DD-OFF}$  before the power can be delivered from the auxiliary winding.

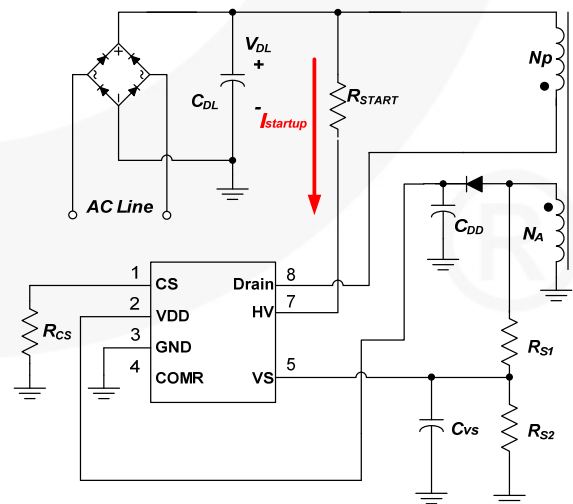


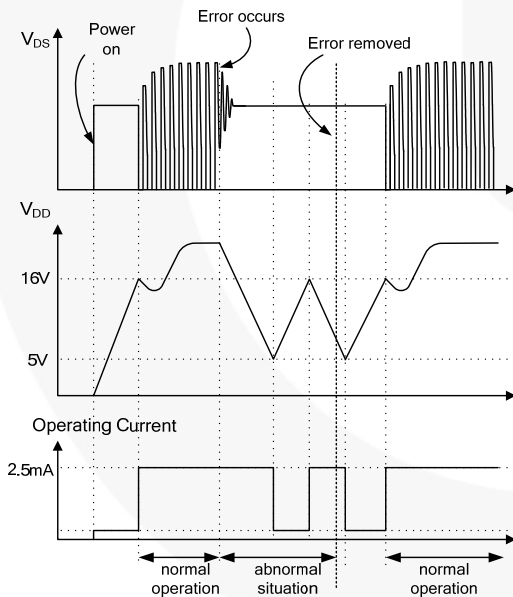
Figure 28. HV Startup Circuit

### Under-Voltage Lockout (UVLO)

The turn-on and turn-off thresholds are fixed internally at 16V and 5V, respectively. During startup, the hold-up capacitor must be charged to 16V through the startup resistor to enable the FSEZ1317A. The hold-up capacitor continues to supply  $V_{DD}$  until power can be delivered from the auxiliary winding of the main transformer.  $V_{DD}$  is not allowed to drop below 5V during this startup process. This UVLO hysteresis window ensures that hold-up capacitor properly supplies  $V_{DD}$  during startup.

### Protections

The FSEZ1317A has several self-protection functions, such as Over-Voltage Protection (OVP), Over-Temperature Protection (OTP), and pulse-by-pulse current limit. All the protections are implemented as auto-restart mode. Once the abnormal condition occurs, the switching is terminated and the MOSFET remains off, causing  $V_{DD}$  to drop. When  $V_{DD}$  drops to the  $V_{DD}$  turn-off voltage of 5V, internal startup circuit is enabled again and the supply current drawn from the HV pin charges the hold-up capacitor. When  $V_{DD}$  reaches the turn-on voltage of 16V, normal operation resumes. In this manner, the auto-restart alternately enables and disables the switching of the MOSFET until the abnormal condition is eliminated (see Figure 29).



**Figure 29. Auto-Restart Operation**

### $V_{DD}$ Over-Voltage Protection (OVP)

$V_{DD}$  over-voltage protection prevents damage from over-voltage conditions. If the  $V_{DD}$  voltage exceeds 24V at open-loop feedback condition, OVP is triggered and the PWM switching is disabled. The OVP has a debounce time (typically 200 $\mu$ s) to prevent false triggering due to switching noises.

### Over-Temperature Protection (OTP)

The built-in temperature-sensing circuit shuts down PWM output if the junction temperature exceeds 140°C.

### Pulse-by-pulse Current Limit

When the sensing voltage across the current-sense resistor exceeds the internal threshold of 0.8V, the MOSFET is turned off for the remainder of switching cycle. In normal operation, the pulse-by-pulse current limit is not triggered since the peak current is limited by the control loop.

### Leading-Edge Blanking (LEB)

Each time the power MOSFET switches on, a turn-on spike occurs at the sense resistor. To avoid premature termination of the switching pulse, a leading-edge blanking time is built in. During this blanking period, the current-limit comparator is disabled and cannot switch off the gate driver. As a result conventional RC filtering can be omitted.

### Gate Output

The FSEZ1317A output stage is a fast totem-pole gate driver. Cross conduction has been avoided to minimize heat dissipation, increase efficiency, and enhance reliability. The output driver is clamped by an internal 15V Zener diode to protect the power MOSFET transistors against undesired over-voltage gate signals.

### Built-In Slope Compensation

The sensed voltage across the current-sense resistor is used for current mode control and pulse-by-pulse current limiting. Built-in slope compensation improves stability and prevents sub-harmonic oscillations due to peak-current mode control. The FSEZ1317A has a synchronized, positive-slope ramp built-in at each switching cycle.

### Noise Immunity

Noise from the current sense or the control signal can cause significant pulsewidth jitter, particularly in continuous-conduction mode. While slope compensation helps alleviate these problems, further precautions should still be taken. Good placement and layout practices should be followed. Avoiding long PCB traces and component leads, locating compensation and filter components near the FSEZ1317A, and increasing the power MOS gate resistance are advised.

## Typical Application Circuit (Primary-Side Regulated Flyback Charger)

Application	Fairchild Devices	Input Voltage Range	Output	Output DC cable
Cell Phone Charger	FSEZ1317AMY_F116	90~265V <sub>AC</sub>	5V/0.7A (3.5W)	AWG26, 1.8 Meter

### Features

- High efficiency (>65.5% at full load) meeting EPS 2.0 regulation with enough margin
- Low standby (Pin<30mW at no-load condition)

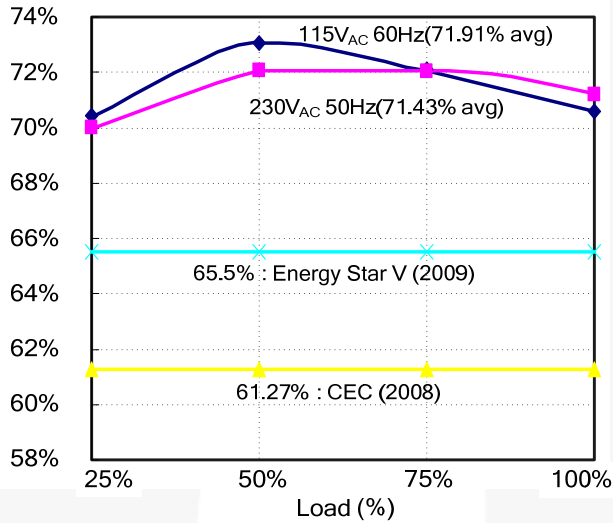


Figure 30. Measured Efficiency

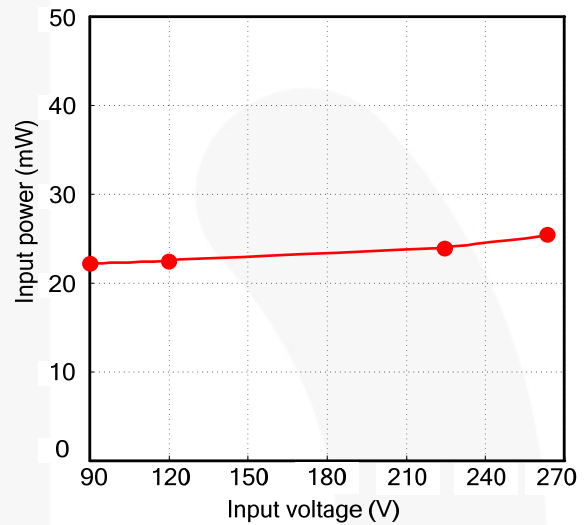


Figure 31. Standby Power

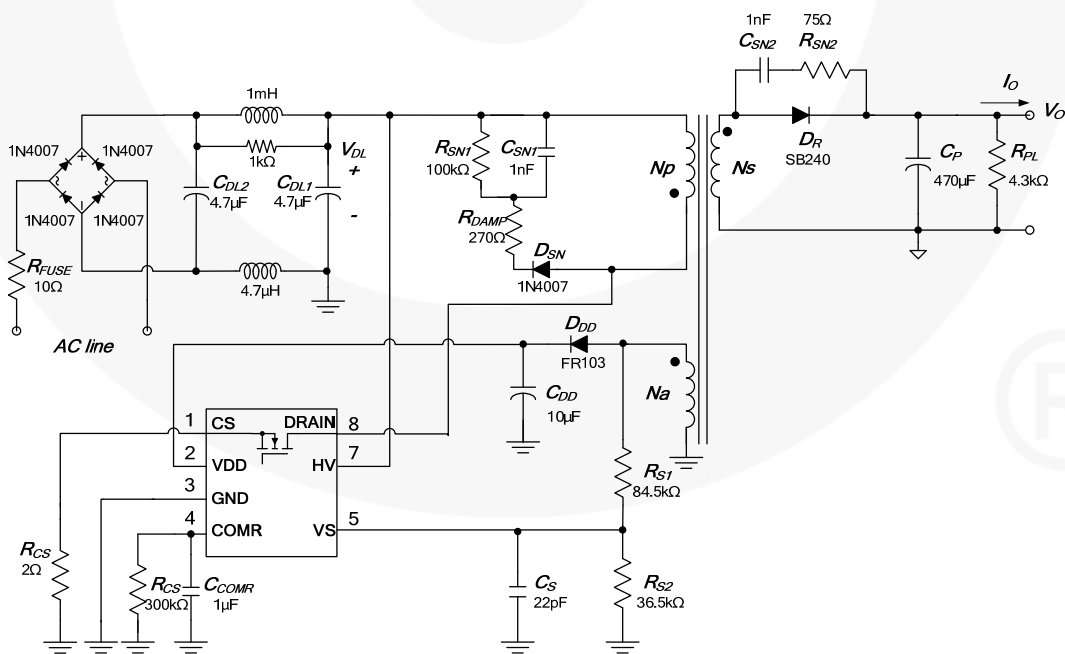


Figure 32. Schematic of Typical Application Circuit

## Typical Application Circuit (Continued)

### Transformer Specification

- Core: EE16
- Bobbin: EE16

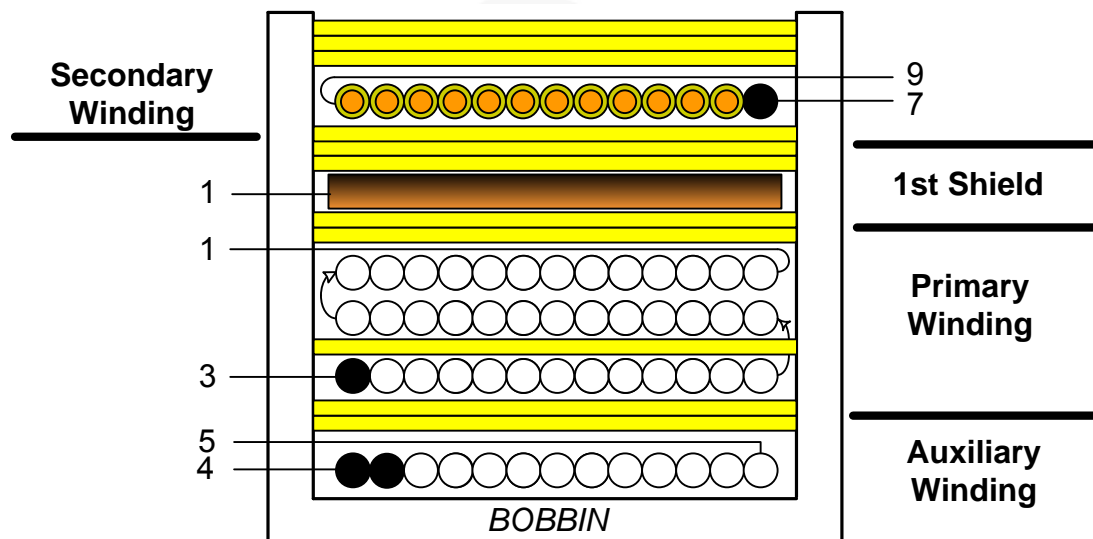


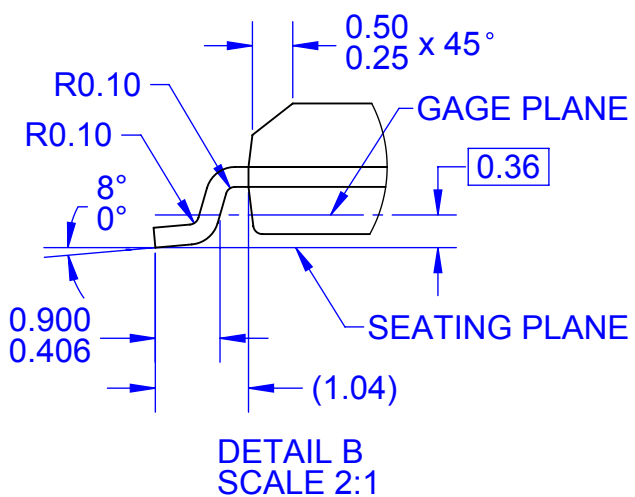
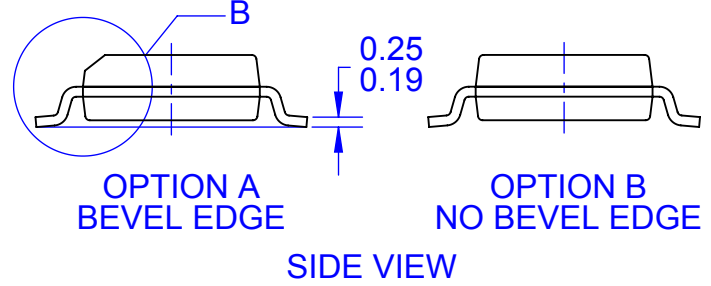
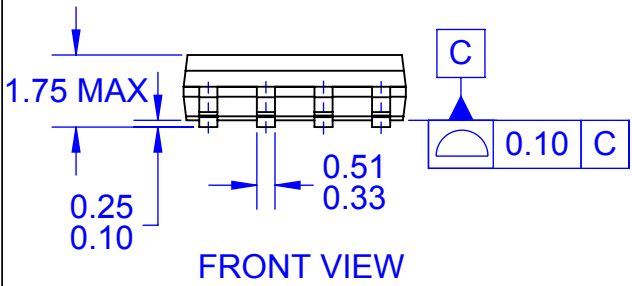
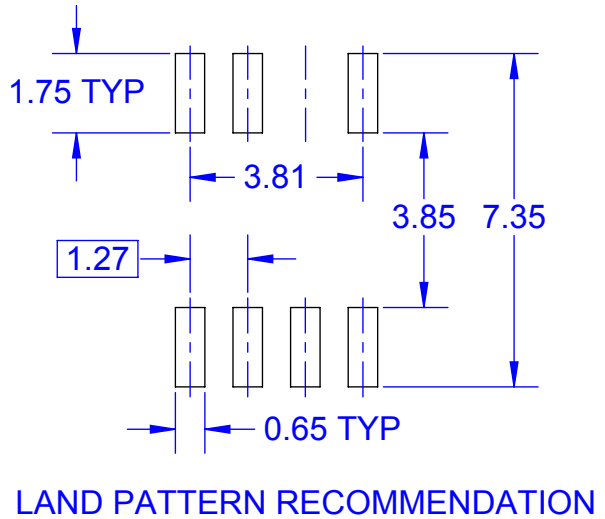
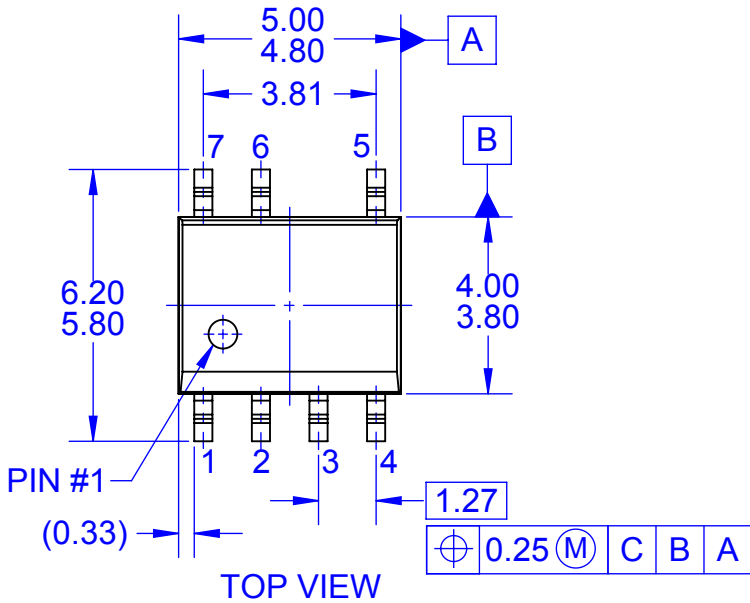
Figure 33. Transformer Specification

#### Notes:

7. When W4R's winding is reversed winding, it must wind one layer.
8. When W2 is winding, it must wind three layers and put one layer of tape after winding the first layer.

No.	Terminal		Wire	$t_s$	Insulation	Barrier Tape	
	S	F				Primary	Seconds
W1	4	5	2UEW 0.23*2	15	2		
W2	3	1	2UEW 0.17*1	41	1		
				39	0		
				37	2		
W3	1		COPPER SHIELD	1.2	3		
W4	7	9	TEX-E 0.55*1	9	3		
			CORE ROUNDING TAPE		3		

	Pin	Specification	Remark
Primary-Side Inductance	1-3	2.25mH $\pm$ 7%	100kHz, 1V
Primary-Side Effective Leakage	1-3	80 $\mu$ H $\pm$ 5%	Short One of the Secondary Windings



- NOTES:
- A. THIS PACKAGE DOES NOT FULLY CONFORM TO JEDEC MS-012, VARIATION AA
  - B. ALL DIMENSIONS ARE IN MILLIMETERS
  - C. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS
  - D. DRAWING FILENAME: MKT-M07Brev4





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